

# N-Channel 150 V (D-S) MOSFET

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PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
150	0.247 at V <sub>GS</sub> = 10 V	15		
	0.255 at V <sub>GS</sub> = 4.5 V	13		

## **FEATURES**

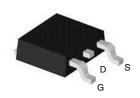
- DT-Trench Power MOSFET
- 175 °C Junction Temperature
- 100 % R<sub>g</sub> Tested



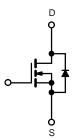
## **APPLICATIONS**

· Primary Side Switch

## TO-252 Pin Configuration



Top View



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)							
Parameter	Symbol	Limit	Unit				
Drain-Source Voltage	V <sub>DS</sub>	150					
Gate-Source Voltage	V <sub>GS</sub>	± 20	V				
Outines Dai Out 1/T 475 00\h	T <sub>C</sub> = 25 °C		15				
Continuous Drain Current (T <sub>J</sub> = 175 °C) <sup>b</sup>	T <sub>C</sub> = 125 °C	l <sub>D</sub>	8.7				
Pulsed Drain Current	I <sub>DM</sub>	45	A				
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	15					
Avalanche Current	I <sub>AR</sub>	12					
Repetitive Avalanche Energy (Duty Cycle ≤ 1 %)	L = 0.1 mH	E <sub>AR</sub>	11.3	mJ			
Maximum Dawar Discination	T <sub>C</sub> = 25 °C	PD	62 <sup>b</sup>	W			
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	٥ ' ا	2.7 <sup>a</sup>	v			
Operating Junction and Storage Temperature Range	•	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C			

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
hungtion to Ambient	t ≤ 10 s	R <sub>thJA</sub>	16	20	°C/W		
Junction-to-Ambient <sup>a</sup>	Steady State		45	55			
Junction-to-Case		R <sub>thJC</sub>	2	2.4			

#### Notes

- a. Surface mounted on 1" x 1" FR4 board.
- b. See SOA curve for voltage derating.



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rameter Symb		Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{DS}$ $V_{GS} = 0 \text{ V, } I_{D} = 250  \mu\text{A}$				V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 150 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C			250		
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	15			Α	
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	0.247				
5 1 2 2 2 2 1 5 1 1 h	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C		0.258		1	
Drain-Source On-State Resistance <sup>b</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C		0.279		Ω	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A		0.255			
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		25		S	
Dynamic <sup>a</sup>							
Input Capacitance	C <sub>iss</sub>			900		pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$		115			
Reverse Transfer Capacitance	C <sub>rss</sub>			70			
Total Gate Charge <sup>c</sup>	$Q_g$			20	25		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		5.5		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			7			
Gate Resistance	$R_g$		1		3.2	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8	12		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 75 \text{ V}, R_L = 5 \Omega$		35	55	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5$		17	25		
Fall Time <sup>c</sup>	t <sub>f</sub>	Ω		30	45		
Source-Drain Diode Ratings and Cha	racteristic (T	<sub>C</sub> = 25 °C)					
Pulsed Current	I <sub>SM</sub>				45	Α	
Diode Forward Voltage <sup>b</sup>	$V_{SD}$	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V		0.9	1.5	V	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, dI/dt = 100 A/μs		55	85	ns	

## Notes:

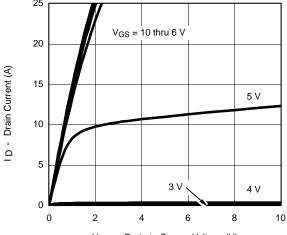
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



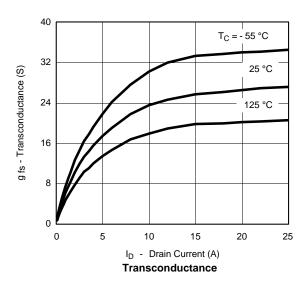
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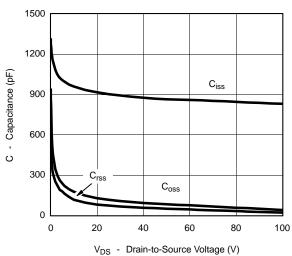
## TYPICAL CHARACTERISTICS (25 °C unless noted)



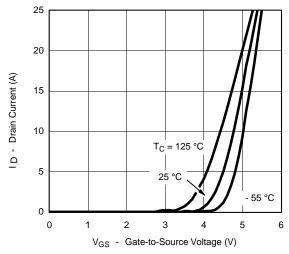
 $V_{\mbox{\scriptsize DS}}\,$  -  $\,$  Drain-to-Source Voltage (V)



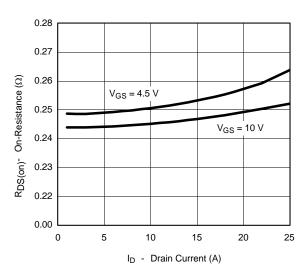




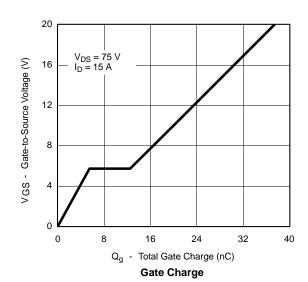
Capacitance



**Transfer Characteristics** 



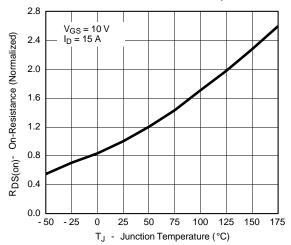
On-Resistance vs. Drain Current





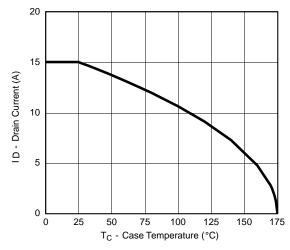


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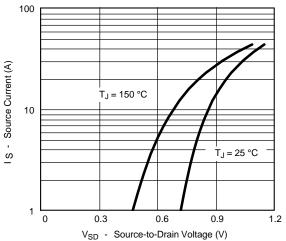


On-Resistance vs. Junction Temperature

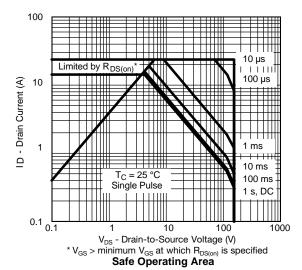
## THERMAL RATINGS



Maximum Avalanche Drain Current vs. Case Temperature



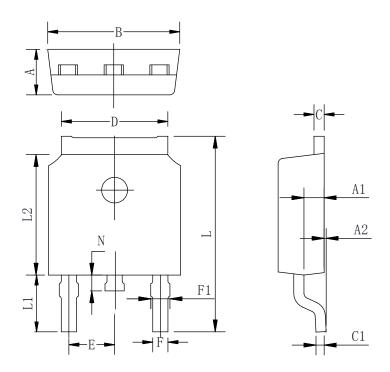
Source-Drain Diode Forward Voltage



Normalized Thermal Transient Impedance, Junction-to-Case

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## **TO-252-2L PACKAGE OUTLINE**



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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